

TRANSMITTAL OF FORMAL DRAWINGSDocket No.
FIS920030199US1In Re Application Of: **Huagie Chen, et al.**

Serial No.	Filing Date	Confirmation No.	Examiner	Art Unit
10/604,607	8/4/03			

Inventor: **STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR CMOS TRANSISTORS
HAVING LATTICE-MISMATCHED SOURCE AND DRAIN REGIONS**Address to:
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Transmitted herewith are:

5 sheets of formal drawing(s) for this application.

☒ Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).A handwritten signature in cursive script, appearing to read "H. Daniel Schnurmann".
*Signature***H. DANIEL SCHNURMANN
AGENT
REGISTRATION NO.: 35,791**Dated: **SEPTEMBER 23, 2003**I certify that this document and attached formal drawings
are being deposited on **September 23, 2003** with the U.S.
Postal Service as first class mail under 37 C.F.R. 1.8 and
addressed to the Commissioner for Patents, P.O. Box 1450,
Alexandria, VA 22313-1450.A handwritten signature in cursive script, appearing to read "Karen Cinq-Mars", followed by the date "9/23/03".
*Signature of Person Mailing Correspondence***Karen Cinq-Mars***Typed or Printed Name of Person Mailing Correspondence*